

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J374R

#### 1. Applications

· Power Management Switches

#### 2. Features

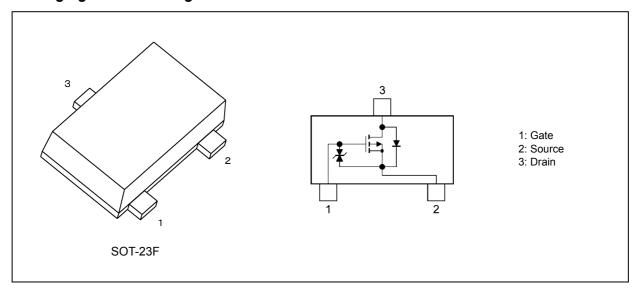
- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 4.0-V gate drive voltage.
- (3) Low drain-source on-resistance

 $R_{DS(ON)} = 71 \text{ m}\Omega \text{ (max) } (@V_{GS} = -10 \text{ V})$ 

 $R_{\rm DS(ON)} = 105 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -4.5 \ {\rm V})$ 

 $R_{DS(ON)} = 136 \text{ m}\Omega \text{ (max) (@V_{GS} = -4.0 V)}$ 

#### 3. Packaging and Pin Assignment



#### 4. Orderable part number

Orderable part number	AEC-Q101 Note			
SSM3J374R,LF	_		General Use	
SSM3J374R,LXGF	YES	(Note 1)	Unintended Use	(Note 1)
SSM3J374R,LXHF	YES		Automotive Use	

Note 1: For more information, please contact our sales or use the inquiry form on our website.



## 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				$V_{DSS}$	-30	V
Gate-source voltage				$V_{GSS}$	-20/+10	
Drain current (DC)			(Note 1)	$I_D$	-4	Α
Drain current (pulsed)			(Note 1), (Note 2)	$I_{DP}$	-16	
Power dissipation			(Note 3)	$P_{D}$	1	W
Power dissipation		(t < 10 s)	(Note 3)	$P_{D}$	2	
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  1 ms, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = -16/+10 V, V <sub>DS</sub> = 0 V	_	_	±10	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	_	_	-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-30	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 10 V	-21	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	$V_{DS}$ = -10 V, $I_{D}$ = -100 $\mu$ A	-0.8	_	-2.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -3.0 A, V <sub>GS</sub> = -10 V	_	54	71	mΩ
			$I_D = -2.0 \text{ A}, V_{GS} = -4.5 \text{ V}$	_	80	105	
			I <sub>D</sub> = -1.0 A, V <sub>GS</sub> = -4.0 V	_	89	136	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.0 A	2.3	4.6	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current  $(I_D)$  to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

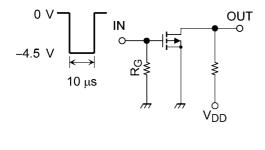
Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 6.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V},$	_	280	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	40	_	
Output capacitance	C <sub>oss</sub>		_	55	_	
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = -15 V, $I_{D}$ = -1.0 A $V_{GS}$ = 0 to -4.5 V, $R_{G}$ = 10 $\Omega$	_	13	_	ns
Switching time (turn-off time)	t <sub>off</sub>	Duty ≤ 1 %, Input: tr, tf < 5 ns Common source	_	22	_	

#### 6.3. Switching Time Test Circuit



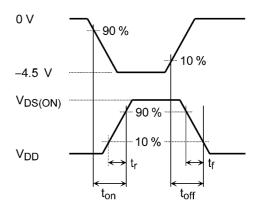


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform

#### 6.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = -15 V, V <sub>GS</sub> = -10 V,	_	5.9		nC
Gate-source charge 1	Q <sub>gs1</sub>	$I_D = -4.0 \text{ A}$	_	0.8		
Gate-drain charge	Q <sub>gd</sub>		_	1.2		



# 6.5. Source-Drain Characteristics (Unless otherwise specified, $T_a$ = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (	Note 1)	$V_{DSF}$	$I_D = 4.0 \text{ A}, V_{GS} = 0 \text{ V}$	_	0.9	1.2	V

Note 1: Pulse measurement.

#### 7. Marking

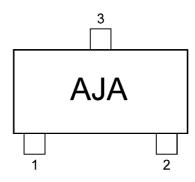


Fig. 7.1 Marking



#### 8. Characteristics Curves (Note)

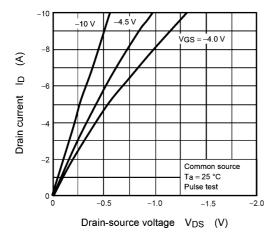


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

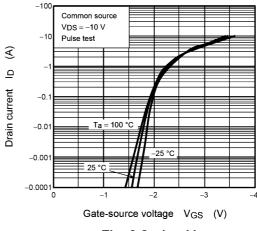


Fig. 8.2 I<sub>D</sub> - V<sub>GS</sub>

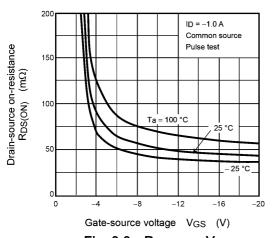


Fig. 8.3  $R_{DS(ON)}$  -  $V_{GS}$ 

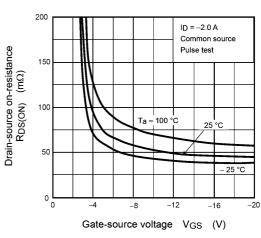


Fig. 8.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

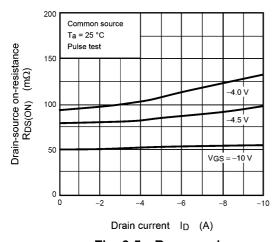


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

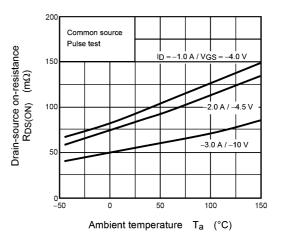
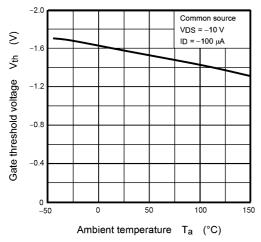
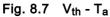


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>







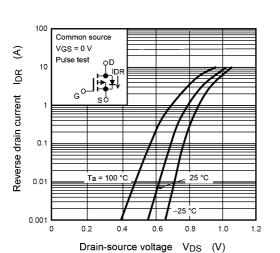


Fig. 8.9 IDR - VDS

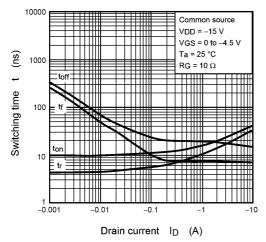


Fig. 8.11 t - I<sub>D</sub>

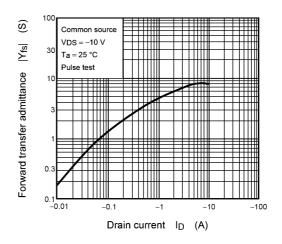


Fig. 8.8 |Y<sub>fs</sub>| - I<sub>D</sub>

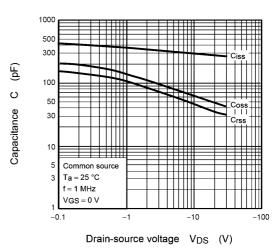


Fig. 8.10 C - V<sub>DS</sub>

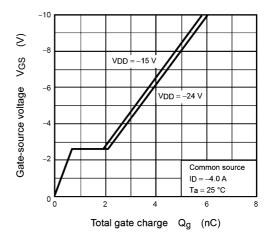
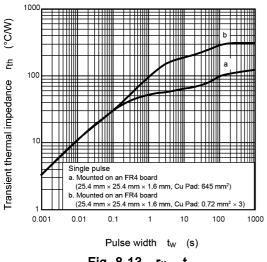


Fig. 8.12 Dynamic Input Characteristic





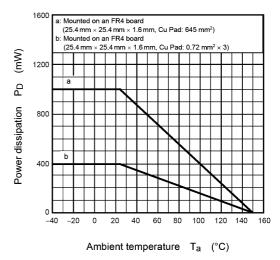


Fig. 8.13 rth - tw

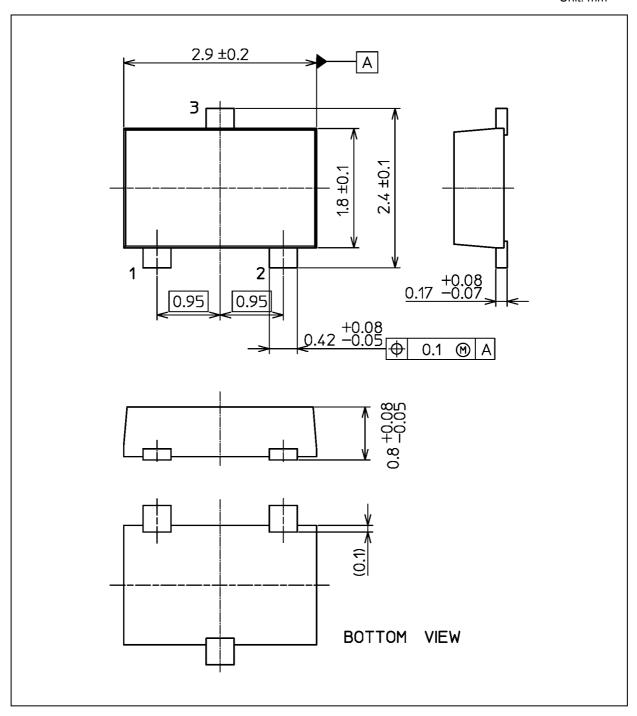
Fig. 8.14 P<sub>D</sub> - T<sub>a</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
TOSHIBA: 2-3Z1S	
Nickname: SOT-23F	

Rev.2.0



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